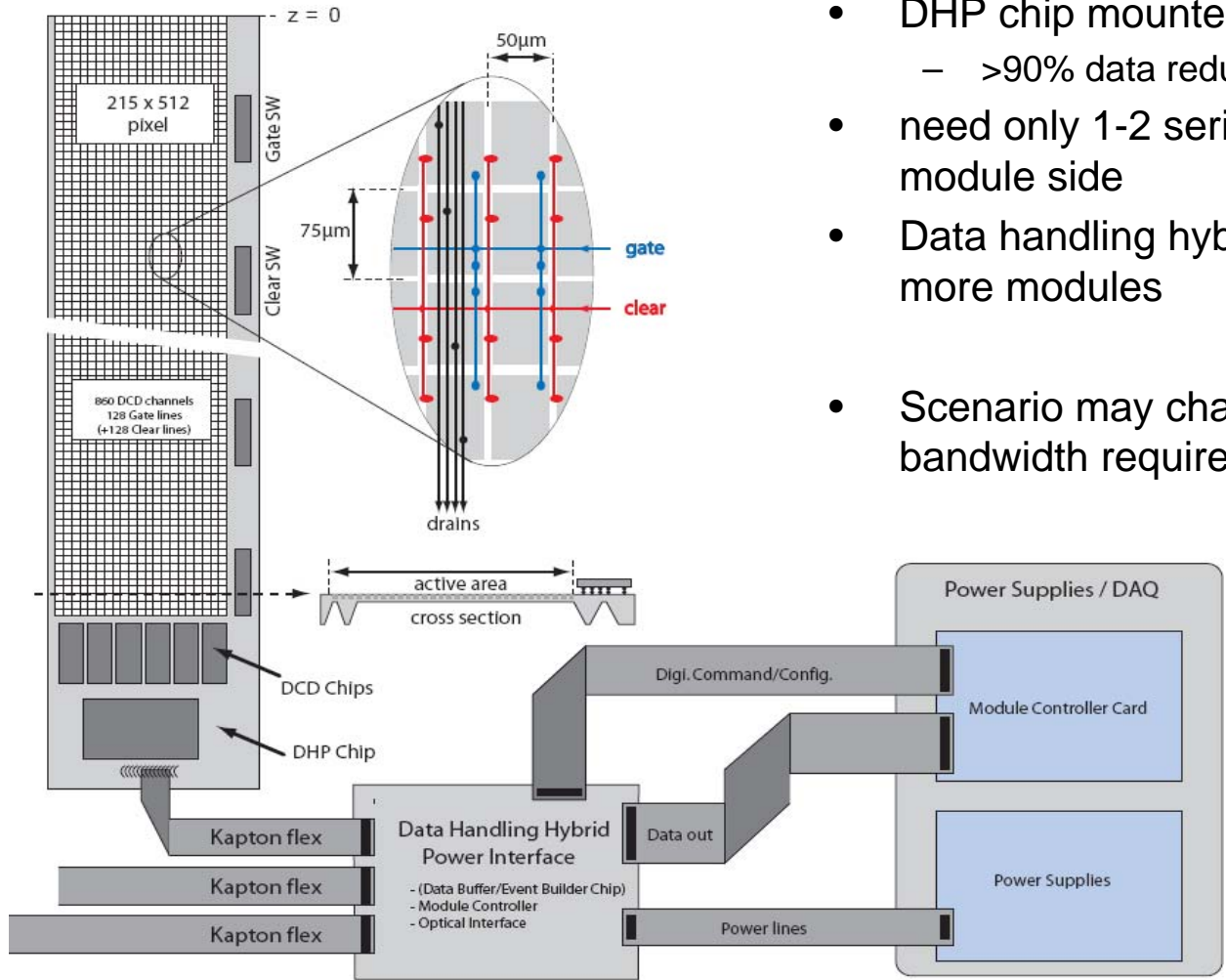


Development of the Data Handling Processor DHP

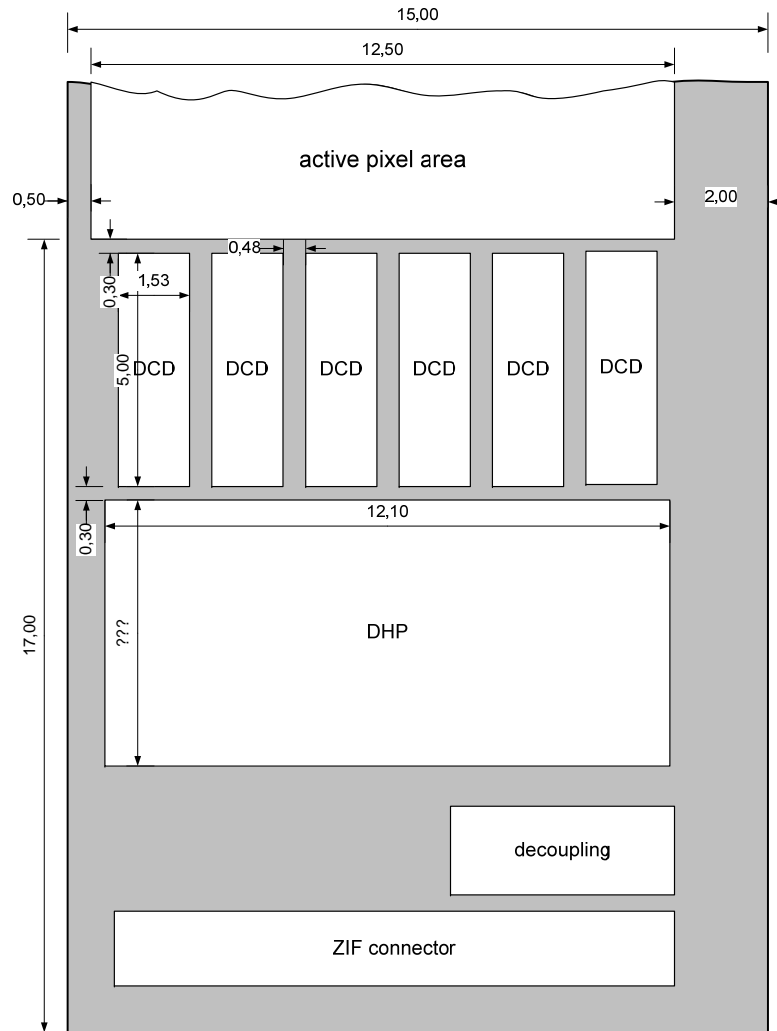
Tomasz Hemperek, Andre Kruth, Hans Krüger, University of Bonn
Albert Comerma, Angel Diéguez, University of Barcelona

- Module layout
- Data rates
- DHP functionality
- Technology / C4 bump bonds
- Work plan



- DHP chip mounted on sensor module
 - >90% data reduction
- need only 1-2 serial links for data out per module side
- Data handling hybrid to support one or more modules
- Scenario may change according to bandwidth requirements

End of Module Layout



DCD

- 150 x 150 μm^2 cells
- 16 rows, 10 columns
- x4 output multiplexing
- 6 chips, 1.5 x 4.7 mm

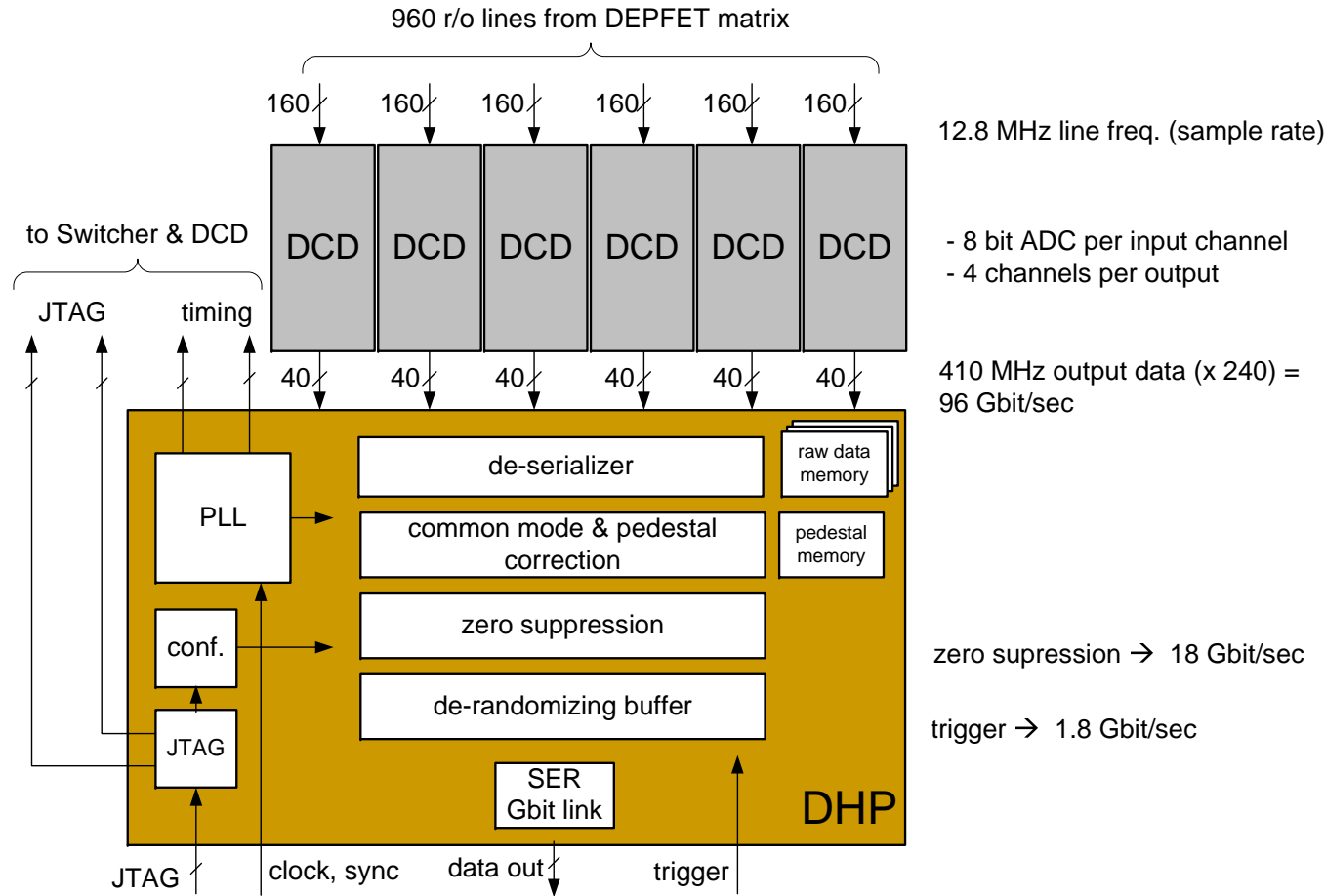
DHP

- 200 μ bump bond pitch
- 12 (6) x ??? mm
- one or two (or more) chips

Connector

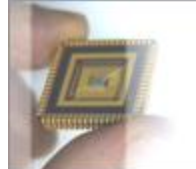
Decoupling

Signal Flow and Data Rates



- ### Assumptions
- 10µs r/o time
 - 128 (switcher) rows
 - 10 kHz trigger rate
 - 5% occupancy

- data processing blocks (synthesized standard cell design)
 - common mode calculation (& correction)
 - pedestal correction
 - de-randomizing buffer
- memory blocks (raw frame data, pedestal correction)
- clock & timing management (PLL, prog. delay lines)
- DACs, slow ADC for monitoring temperature etc.
- slow control interface: JTAG
- Gigabit serial transmitter (LVDS, CML...)



Participation of UB in the DEPFET collaboration tasks

ASIC Development

Switcher

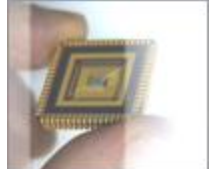
DCD

Data Handling Processor (DHP)

Data link

Synchronisation switcher/readout
Beam clock synchronization
Trigger handling
Data control (up/download configuration data)
Slow control (currents, temperatures)
Memory to buffer 10 frames
Pedestal Memory needed for 0-suppression
Eventually common mode suppression
Readout buffer holding 4 0-suppressed frames
IO modules

[+ integration



Participation of UB in the DEPFET collaboration tasks

Meeting in Barcelona, November 11th, 2008

Phone meeting, March 25th, 2009

JTAG interface for slow control (designer Albert Comerma)

Bandgap reference (designer Eva Vilella)

DAC (8 bit, slow) (designer Lluís Freixes)

ADC (10-12 bit, slow)

Standar LVDS

Input differential amplifier (it is still not clear->ARM IP?)

Progress

Agreements with MOSIS/IBM/ARM signed (Nov'08-Feb'09)

Design kit for cms9lp and libraries ready (Mar'09)

Design of bandgap an DAC started. Scheduled for June.

Other modules scheduled for October.

In principle the DAC will be C-based. The ADC will be probably based on the DAC (SAR). JTAG from Synopsys.

Interface to DCD

- DHP → DCD
 - BitCLK (LVDS)
 - FrameSYNC (LVDS)
 - Row2SYNC (LVDS)
 - JTAG interface for configuration and boundary scan (1.8V CMOS)

- DCD → DHP
 - 4 to1 multiplexed ADC data per output, 400MHz
 - single-ended inputs
(differential input stage with common threshold, set by DCD)
 - no input termination
 - BitCLK, Row2SYNC return for testing and synchronization

Interface to Switcher

- Shift register based channel selection (all LVDS)
 - CLK
 - SEROUT
 - SERIN
 - GateStrb
 - ClearStrb

- JTAG slow control (1.8V CMOS)
 - TCK, TMS, TDI, TDO

Interface to DHH

- DHH → DHP (all LVDS)
 - RowCLK (12.7 MHz, f0/40)
 - FrameSYNC (abort gap clock)
 - Trigger
 - JTAG (CMOS?)

- DHP → DHH
 - DataOUT: one or two GBit links (LVDS or CML)
 - protocol ?

- SuperKEKB RF frequency $f_0 = 508 \text{ MHz}$ (508.89 MHz precisely)
- Number of slots per cycle: 5120
- Circulation time: 10.061 μs
- System clock $f_0/12 = 42.3 \text{ MHz}$ (or $f_0/4$, $f_0/8$, $f_0/16$, $f_0/256$)
- Abort gap: 200 ns (~100 bunches)
- Clock for abort gap available (**frame clock**)

- DEPFET read-out **synchronous** with **beam circulation** (128 rows):
row clock = $508 \text{ MHz} / (5120/128) = 508 \text{ MHz} / 40 = 12.7 \text{ MHz}$
- Use **$f_0/8$** and divide by 5 (DHH?)

- 130 nm good for analogue performance (i.e. clock management chip DCM), many function blocks and libraries readily available
- But: 90 nm better for digital performance and size constraints (end of stave)
- Chip area function limited → same functionality in 90nm (~4k/mm²) not more expensive than 130nm (~2k/mm²)

Vendor (90 nm)		min. block size [mm ²]	price [\$]	price [€]	price/mm ² [€]	bump bond pitch [µm]
UMC (Europractice)	std. MPW	16		41.800	2.613	162 ?
	mini@sic	3.5		7.000	1.991	
IBM (MOSIS)	std. MPW	16	100.000	62.500	3.906	200 ✓
	min	4	25.000	15.625	3.906	
TSMC (Europractice)	std. MPW	16	89.910	56.194	3.512	180
	mini@sic	4	9.850	6.156	1.539	
Chartered (own MPW runs)	???					

C4 Bump Bonding @ IBM

- C4 bump bonds option for MPW available (130nm and 90nm)
- Costs: \$ 8.000 per engineering lot (for extra wavers + bumps)
- technology options:

design	bump \varnothing	pitch	availability
3 on 6	?	150 μ	(mentioned in the design document) MPW?
4 on 6	100μ (130μ, HTS)	200μ	MPW via MOSIS
5 on 10	130 μ (146 μ , HTS)	250 μ	MPW via MOSIS

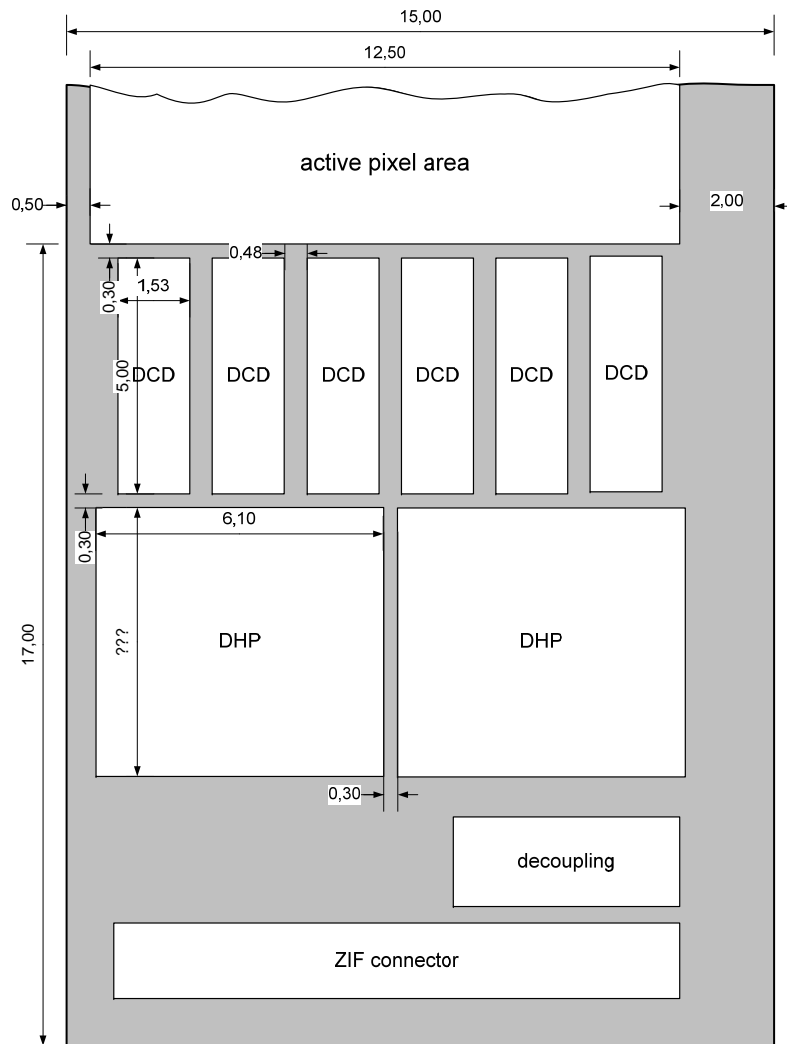
solder type		reflow temp.	UBM
HTS	Pb97Sn3	345°C-375°C (215°C-255°C with mod.)	TiW/Cr/Cu/Cu (Ni barrier option)
LTS	Sn99.5Ag0.5	235°C-255°C	?

- ADC **resolution** of the DCD (8 or 6 bit or variable)
- Frame timing: 10 or 20 μ s
- **Trigger rate**
- Number of (electrical) **rows**: 128 or 256
- DCD output data format and synchronization timing
- SEU hardness?
- Interface to DHH (cable, protocol)
- ...

Need to have these numbers fixed !

- Chip size, bump bond footprint
- Memory size
- Data bus width
- ...

End of Module Layout – split DHP



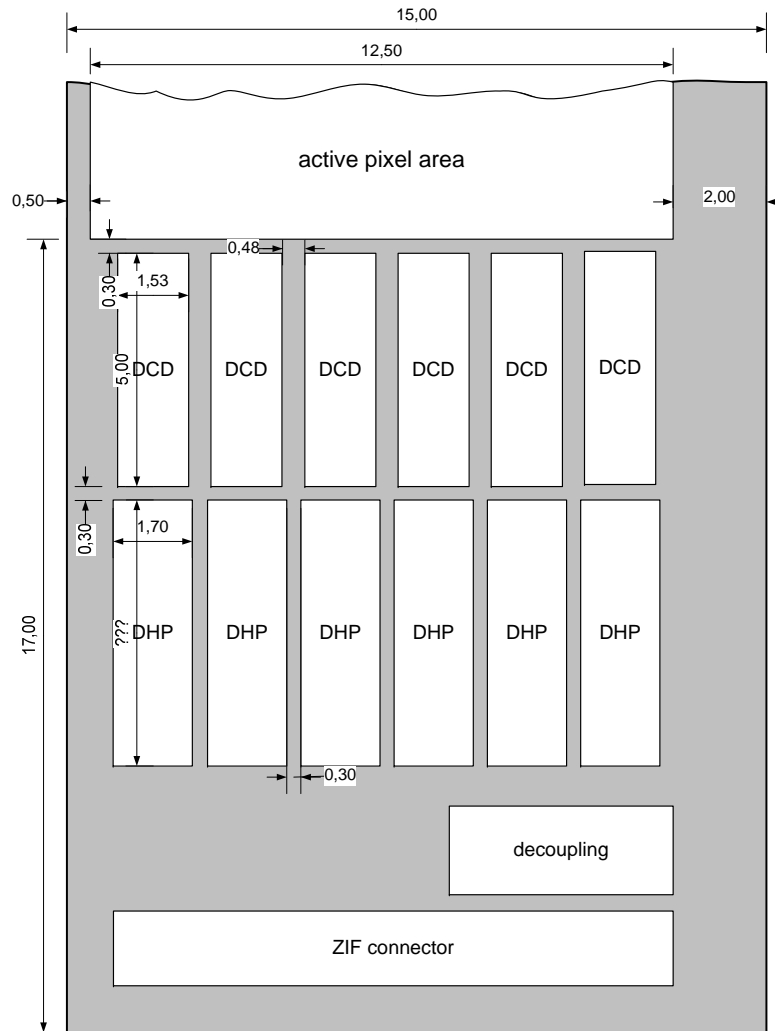
DCD

- **150 μm x 150 μm cells**
- 6 chips, 1.5 x 4.7 mm
- Input: 16 rows, 10 columns
- Output: **4 rows**, 10 columns

DHP

- **200 μm bump bond pitch**
- 2 chips
- 6.1 x ??? mm
- Input: **4 rows**, 30 columns

End of Module Layout – ‘one to one’



DCD

- **150 μm x 150 μm cells**
- 6 chips, 1.5 x 4.7 mm
- Input: 16 rows, 10 columns
- Output: **4 rows, 10 columns**

DHP

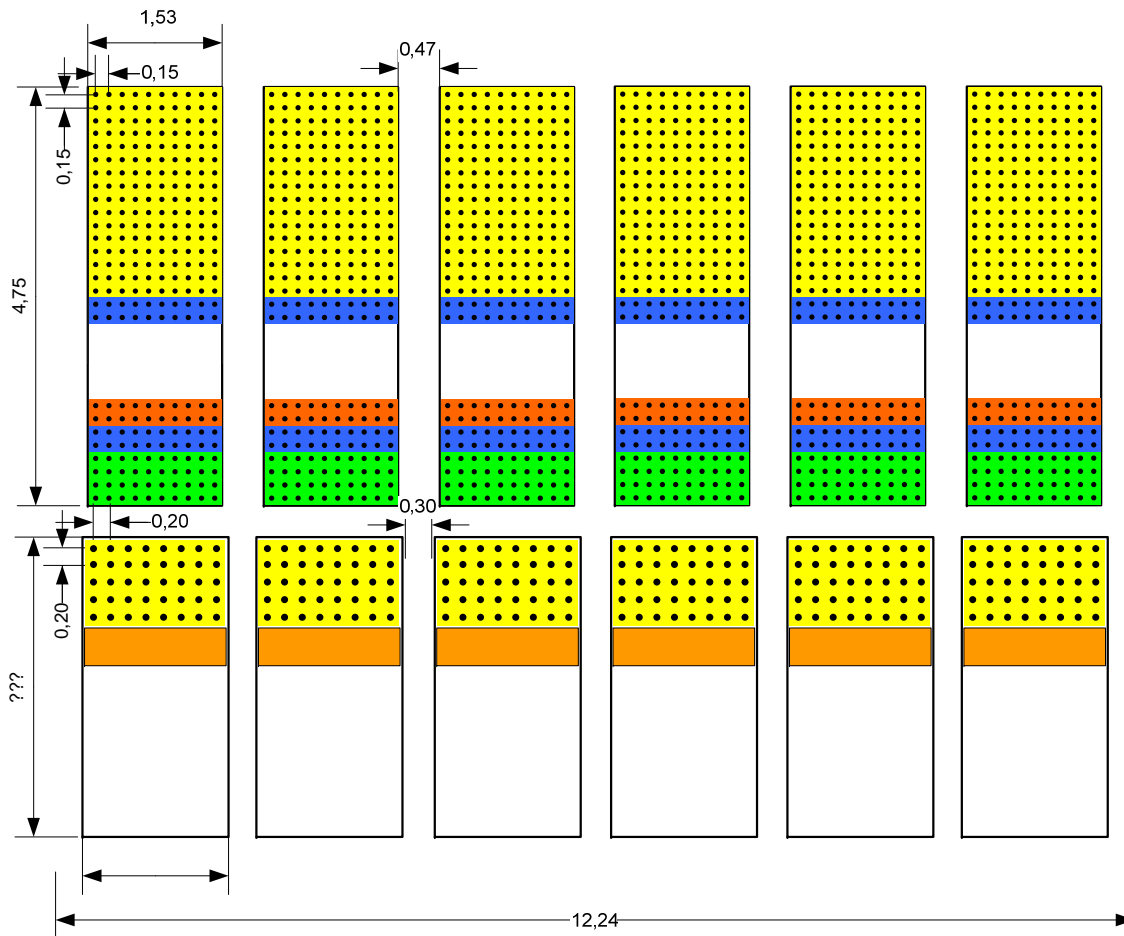
- **200 μm bump bond pitch**
- 6 chips
- 1.7 x ??? mm
- One 1Gbit link per DHP
→ **6 Gbit per module**
- Need to change input layout:
 - **5 rows, 8 columns**

Next steps

- Test chip with full custom analog blocks (October 2009)
 - basic data processing flow (synthesized)
 - diff. input, Gbit LVDS driver
 - DAC, Iref...
- DHP 0.1 (Q2 2010)
 - full data processing
 - 40 inputs (fits to one DCD chip)
 - bump bond IOs
- DHP 1.0 (Q1 2011)
 - full chip (40, 120 or 240 inputs ...)

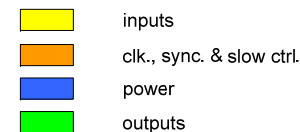
Specs to be negotiated → synchronize with DCD development

DCD + DHP footprints



6 chip DHP option

- Further reduced costs
- one Gbit link per chip @ 6 Gbit r/o per module
- but: even more redundant logic
- Need to change input pad layout
 - DCD: 4 x 10 @ 150 μ
 - DHP: 5 x 8 @ 200 μ



DHP Data Processing

